



公司簡介

MOCVD 創造世界級之競爭力

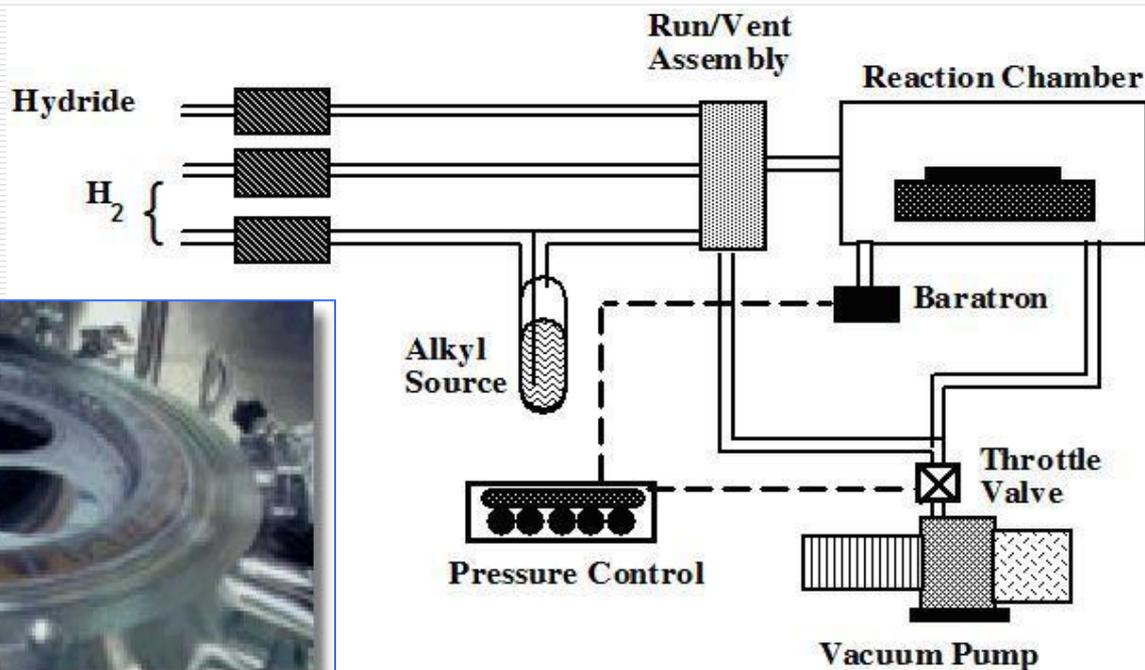




核心技術

MOCVD (有機金屬氣相沉積法)

- Metal Organic Chemical Vapor Deposition





核心技術

生產
機台

MOCVD有機金屬化學氣相沉積法
Metal Organic Chemical Vapor Deposition

生產
方式

透過有機金屬化學氣相沉積法，在基板上生長半導體薄膜的方式，同時透過機台即時監控，精確控制磊晶層，完成砷化鎵、磷化銦、氮化鎵等不同產品磊晶片生產。

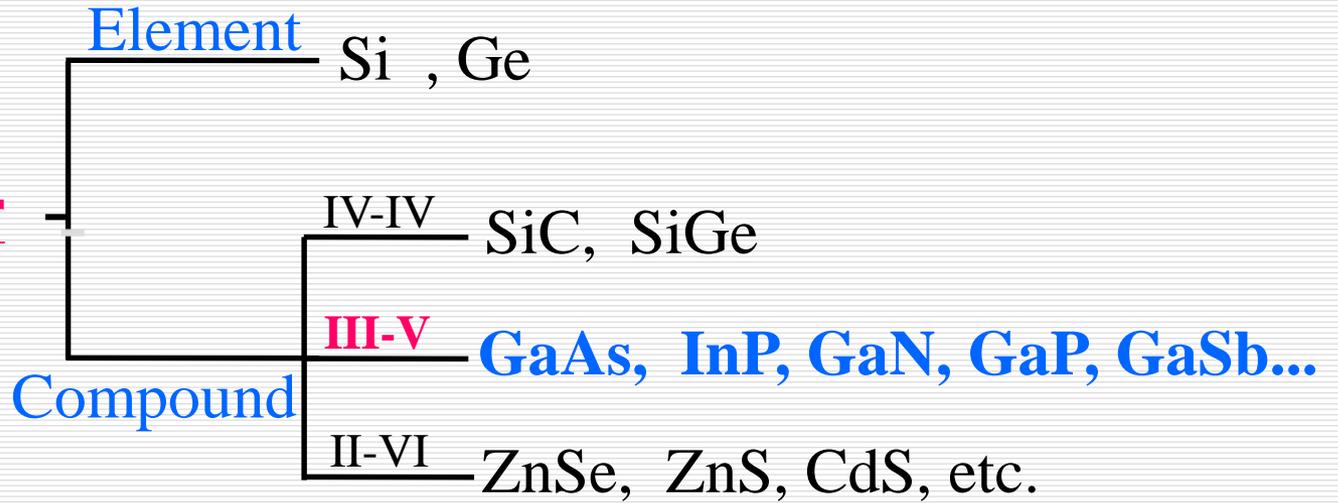
生產
原理

磊晶層是由MOCVD在腔體中加熱基板，一個原子層，層層堆疊，行成磊晶層。



半導體分類 (依使用材料)

Semiconductor



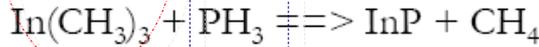
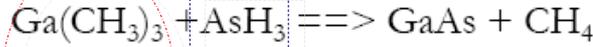
Period	Column II	III	IV	V	VI
2	Be 鈹 Beryllium	B 硼 Boron	C 碳 Carbon	N 氮 Nitrogen	O 氧 Oxygen
3	Mg 鎂 Magnesium	Al 鋁 Aluminum	Si 矽 Silicon	P 磷 Phosphorus	S 硫 Sulfur
4	Zn 鋅 Zinc	Ga 鎵 Gallium	Ge 鍺 Germanium	As 砷 Arsenic	Se 硒 Selenium
5	Cd 鎘 Cadmium	In 銦 Indium	Sn 錫 Tin	Sb 銻 Antimony	Te 碲 Tellurium
6	Hg 汞 Mercury	Tl 鉈 Thallium	Pb 鉛 Lead		

- 二元化合物 Binary : GaAs, InP, GaP, GaN, etc.
- 三元化合物 Ternary : InGaAs, InGaP, AlGaAs, etc.
- 四元化合物 Quaternary : AlGaInP, InGaAsP, etc.
- 五元化合物 Pentanary : AlGaInAsN, etc.



磊晶過程中之化學反應

化學反應式：



主要原物料：

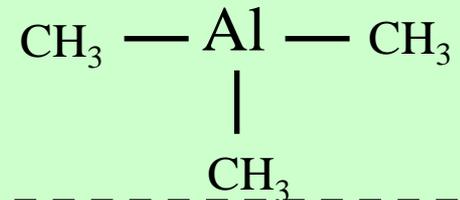
MO Source + **Hydride** + Carrier Gas : **H₂**

TEAl : Tri-ethyl-Aluminum (C₂H₅)₃Al
 TMGa : Tri-Methyl-Gallium (CH₃)₃ Ga
 TMIn : Tri-Methyl-Indium (CH₃)₃In
 DETe : Di-ethyl-Tellurium (C₂H₅)₂Te
 DEZn : Di-ethyl-Zinc (C₂H₅)₂Zn
 CP₂Mg : Bis (cyclo-penta-dienyl) Magnesium 環戊二烯鎂

AsH₃ : Arsine
 PH₃ : Phosphine
 SiH₄ : Silane
 Si₂H₆ : Disilane
 H₂Se : Hydrogen Selenide
 CBr₄ : Carbon Tetrabromide

TMAI Tri - Methyl - Aluminum (CH₃)₃Al

三 甲 基 鋁





化合物半導體材料特性

1. High Electron Mobility 高電子移動速率 (5.7x higher than CMOS)
2. High Frequency Response 高頻率響應
3. Wide Band Width 寬幅之頻寬
4. High Linearity 高線性度
5. High Power 高功率
6. Alternative Choice of Material 材料選擇多元性
7. 抗輻射

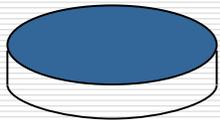
適用於微電子產品—HBT、pHEMT、BiHEMT、GaN on XX
光電子產品—PIN (PD、APD)、VCSEL、LD、SC



微電子產品 產業供應鏈

Sumitomo, Freiberg, AXT

2~6 "GaAs Substrate

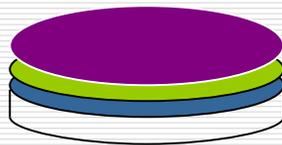


GaAs Epi- Wafer
磊晶片



MOCVD Reactor

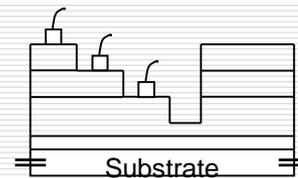
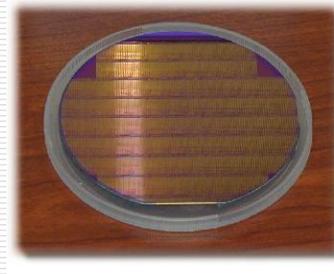
VPEC is a Pure
Epi Provider



IDM : Qorvo, Skyworks

Fabless : Avago,
Qualcomm, Richwave,

Microelectronics
IC Process



Foundry :
WIN, AWSC



Wireless
Communication



IC Package & Testing

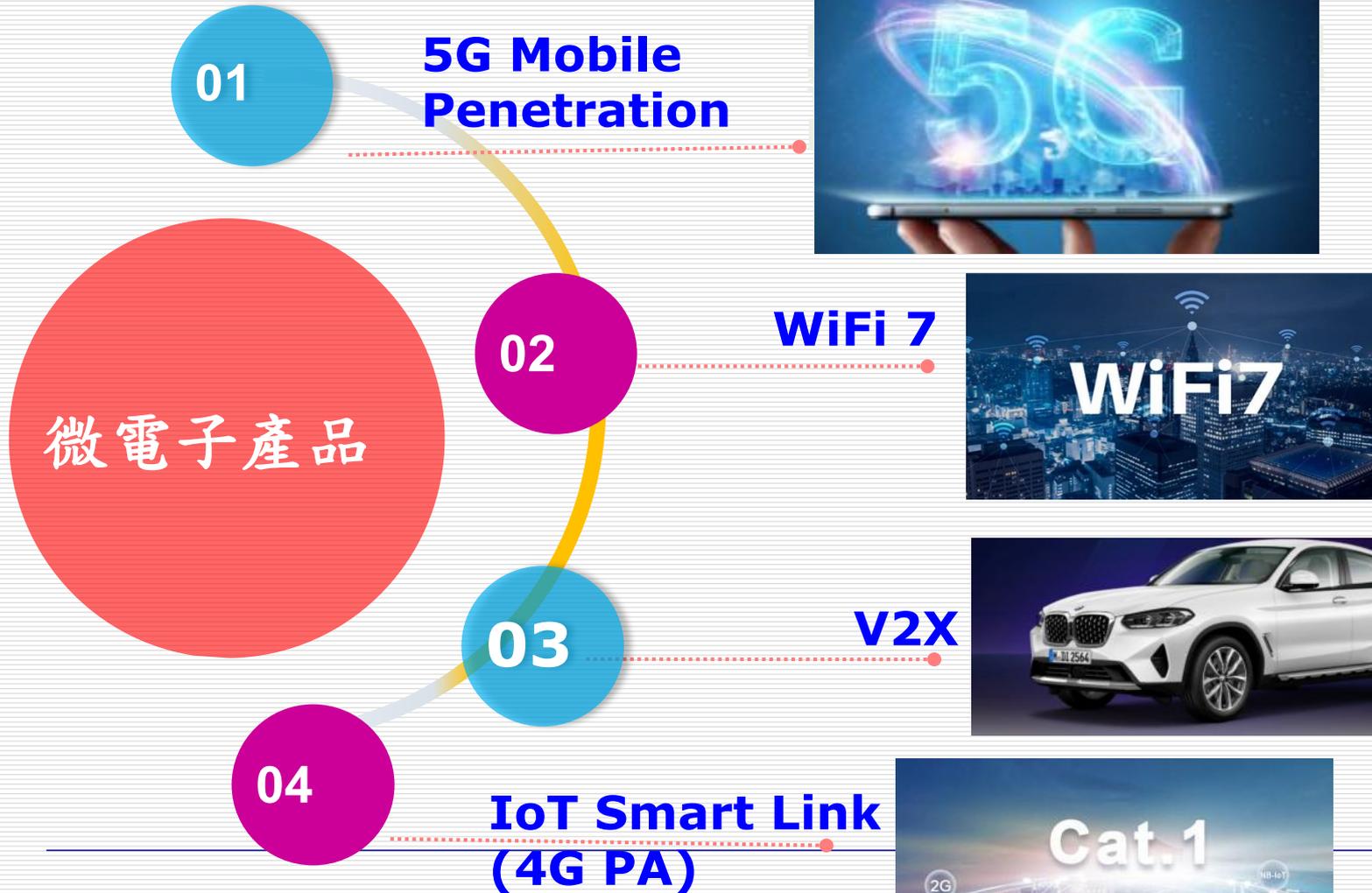


2022年-2025年Q1損益情形

	2025 Q1	%	2024	%	2023	%	2022	%
Revenue	793,663	100%	3,241,217	100%	2,694,104	100%	2,603,629	100%
Gross margin	316,671	40%	1,278,964	39%	1,108,914	41%	1,089,007	42%
Operating Profit	178,983	23%	721,214	22%	542,069	20%	579,950	22%
Non-operating income & expense	17,638	2%	96,460	3%	-347	0%	87,533	3%
Tax	-39,334	-5%	-146,619	-5%	-91,490	-3%	-122,755	-5%
Net income	157,287	20%	671,055	21%	450,232	17%	544,728	21%
EPS	0.85		3.63		2.43		2.95	



2025 Outlook





2025 Outlook



01 Data Center High Speed Connectivity



PD for 800G
VCSEL for 400G

02 3D-sensing



VCSEL / PD

03 AR/VR



VCSEL

04 Future Driving Engines

機器視覺



P-sensor 、 3D Sensing & ToF

LEO Solar Cell



Car LiDAR (LD/PD)



AI glass

矽光子

